

# MOSFET – N-Channel, SUPERFET II, FRFET 600 V, 76 A, 41 mΩ

## FCH041N60F-F085

### Description

SUPERFET® II MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently SUPERFET II is very well suited for the Soft switching and Hard Switching topologies like High Voltage Full Bridge and Half Bridge DC-DC, Interleaved Boost PFC, Boost PFC for HEV-EV automotive. SUPERFET II FRFET® MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.

### Features

- Typical  $R_{DS(on)}$  = 36 mΩ at  $V_{GS} = 10$  V,  $I_D = 38$  A
- Typical  $Q_{g(tot)}$  = 267 nC at  $V_{GS} = 10$  V,  $I_D = 38$  A
- Low Effective Output Capacitance (Typical  $C_{oss(eff.)}$  = 720 nF)
- 100% Avalanche Tested
- Qualified to AEC Q101 and PPAP Capable
- This Device is Pb-Free and is RoHS Compliant

### Applications

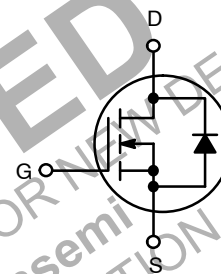
- Automotive On Board Charger
- Automotive DC/DC Converter for HEV



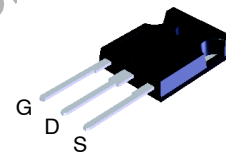
ON Semiconductor®

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$V_{DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
600 V	41 mΩ	76 A

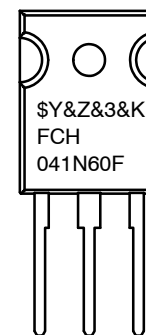


N-Channel MOSFET



TO-247  
CASE 340CK

### MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Data Code (Year & Week)
&K	= Lot Code
FCH041N60F	= Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FCH041N60F–F085

## MAXIMUM RATINGS (T<sub>C</sub> = 25°C, unless otherwise specified)

Symbol	Parameter	Ratings	Unit
V <sub>DSS</sub>	Drain to Source Voltage	600	V
V <sub>GS</sub>	Gate to Source Voltage	±20	V
I <sub>D</sub>	Drain Current – Continuous (V <sub>GS</sub> = 10) T <sub>C</sub> = 25°C	76	A
	Pulsed Drain Current	See Fig. 4	
E <sub>AS</sub>	Single Pulsed Avalanche Rating (Note 1)	2025	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 2)	50	
P <sub>D</sub>	Power Dissipation	595	W
	Derate Above 25°C	4.76	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature (Note 3)	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Starting T<sub>J</sub> = 25°C, L = 18 mH, I<sub>AS</sub> = 15 A, V<sub>DD</sub> = 100 V during inductor charging and V<sub>DD</sub> = 0 V during time in avalanche.
2. I<sub>SD</sub> ≤ 38 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ 380 V, starting T<sub>J</sub> = 25°C.
3. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design, while R<sub>θJA</sub> is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max.	0.21	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient, Max.	40	

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Reel Size	Tape Width	Quantity
FCH041N60F–F085	FCH041N60F	TO-247	–	–	30

# FCH041N60F-F085

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	600	–	–	V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 25°C	–	–	10	μA
		V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150°C (Note 4)	–	–	1	mA
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±20 V	–	–	±100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	3	4	5	V
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 38 A, T <sub>J</sub> = 25°C	–	36	41	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 38 A, T <sub>J</sub> = 150°C (Note 4)	–	89	98	mΩ

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz	–	10900	–	pF
C <sub>oss</sub>	Output Capacitance		–	360	–	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		–	4.4	–	pF
C <sub>oss(eff.)</sub>	Effective Output Capacitance	V <sub>DS</sub> = 0 V to 480 V, V <sub>GS</sub> = 0 V	–	720	–	pF
R <sub>g</sub>	Gate Resistance	f = 1 MHz	–	0.7	–	Ω
Q <sub>g(TOT)</sub>	Total Gate Charge	V <sub>DD</sub> = 380 V, I <sub>D</sub> = 38 A, V <sub>GS</sub> = 10 V	–	267	347	nC
Q <sub>g(th)</sub>	Threshold Gate Charge		–	20	26	nC
Q <sub>gs</sub>	Gate to Source Gate Charge		–	59	–	nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge		–	106	–	nC

### SWITCHING CHARACTERISTICS

t <sub>on</sub>	Turn-On Time	V <sub>DD</sub> = 380 V, I <sub>D</sub> = 38 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 4.7 Ω	–	–	242	ns
t <sub>d(on)</sub>	Turn-On Delay Time		–	63	–	ns
t <sub>r</sub>	Rise Time		–	48	–	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		–	214	–	ns
t <sub>f</sub>	Fall Time		–	33	–	ns
t <sub>off</sub>	Turn-Off Time		–	–	514	ns

### DRAIN-SOURCE DIODE CHARACTERISTICS

V <sub>SD</sub>	Source to Drain Diode Voltage	I <sub>SD</sub> = 38 A, V <sub>GS</sub> = 0 V	–	–	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 38 A, dI <sub>SD</sub> /dt = 100 A/μs	–	219	–	ns
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>DD</sub> = 480 V	–	1.9	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at T<sub>J</sub> = 150°C. Product is not tested to this condition in production.

## TYPICAL CHARACTERISTICS

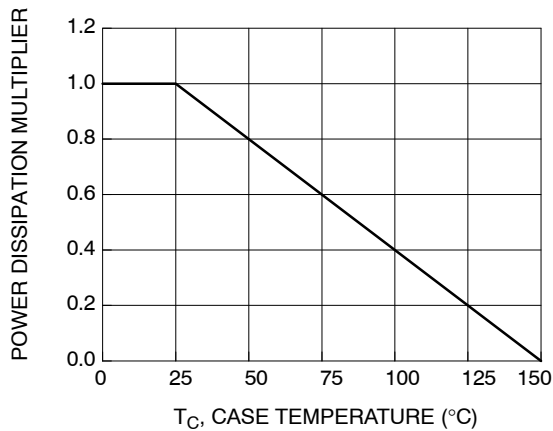


Figure 1. Normalized Power Dissipation vs. Case Temperature

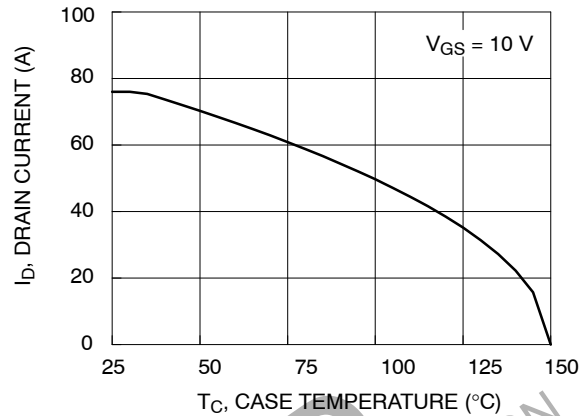


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

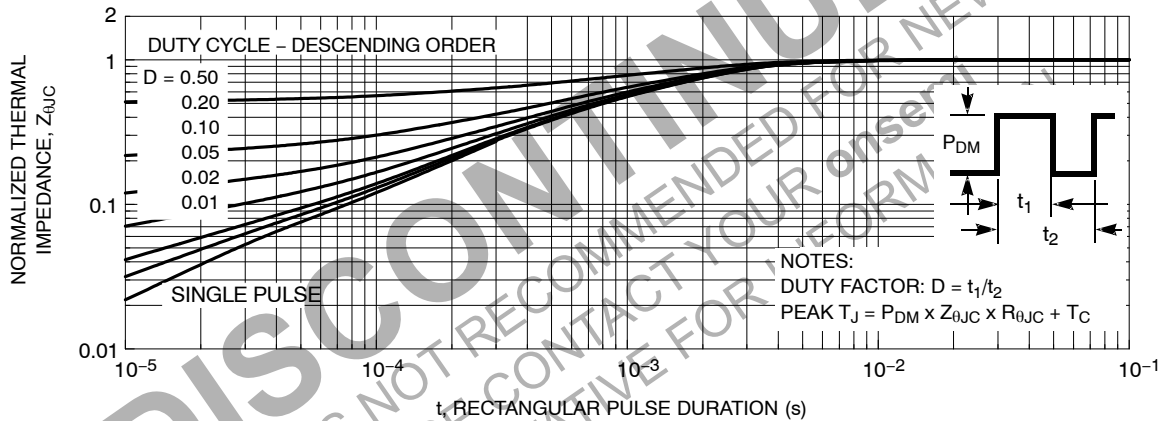


Figure 3. Normalized Maximum Transient Thermal Impedance

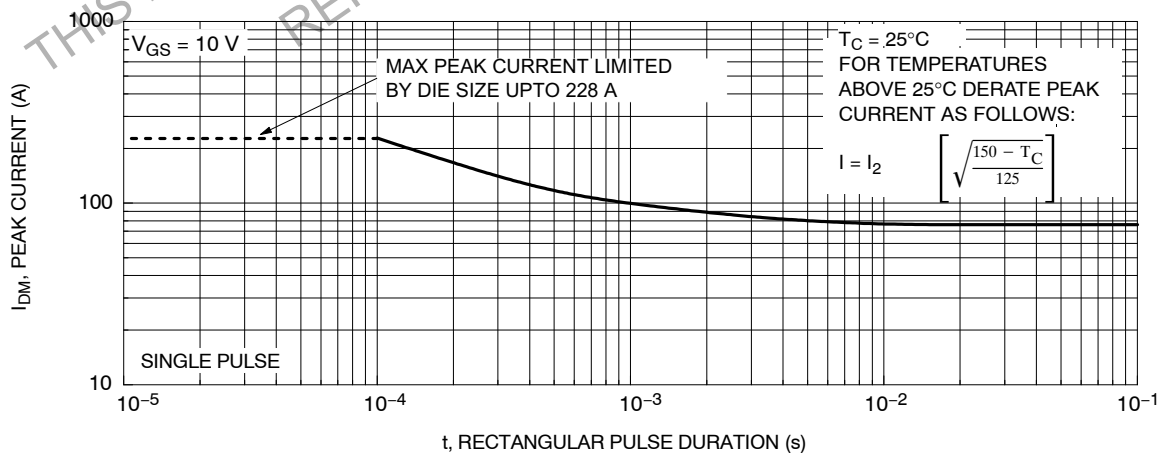


Figure 4. Peak Current Capability

## TYPICAL CHARACTERISTICS (continued)

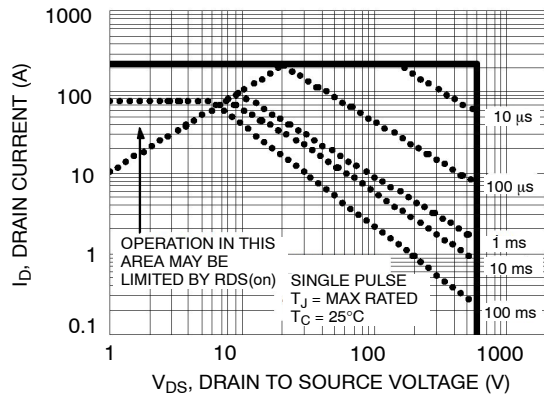


Figure 5. Forward Bias Safe Operating Area

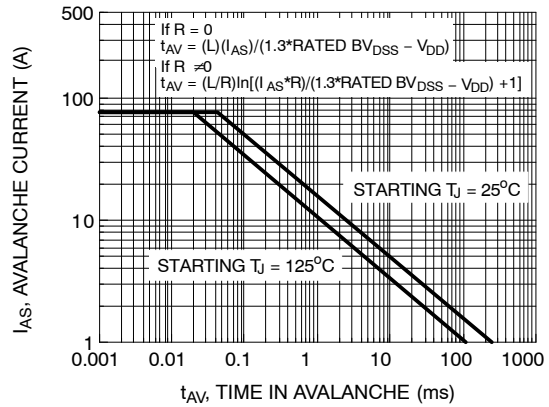


Figure 6. Unclamped Inductive Switching Capability

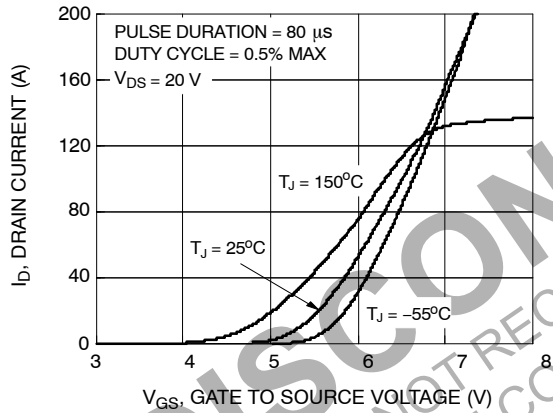


Figure 7. Transfer Characteristics

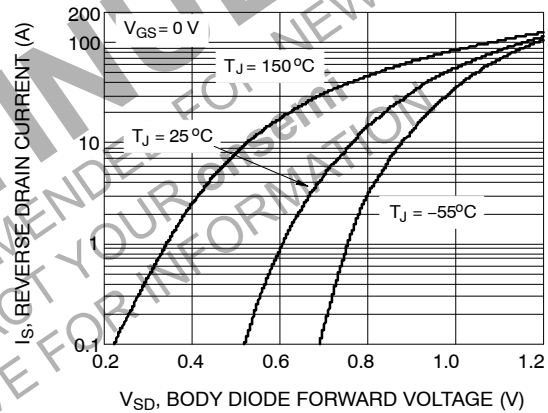


Figure 8. Forward Diode Characteristics

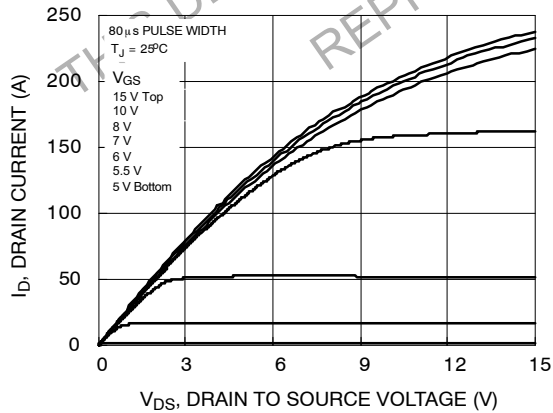


Figure 9. Saturation Characteristics

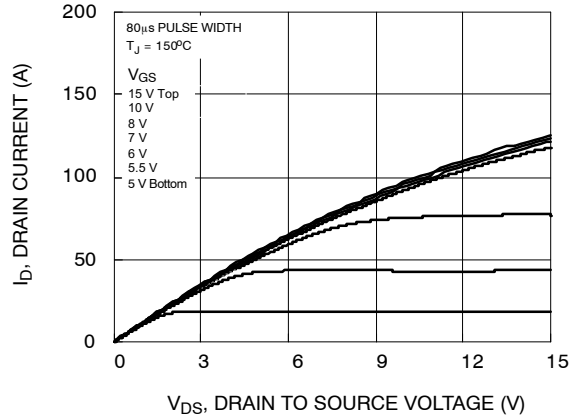


Figure 10. Saturation Characteristics

## TYPICAL CHARACTERISTICS (continued)

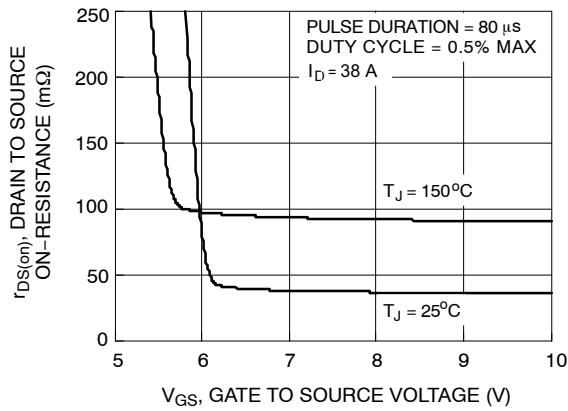
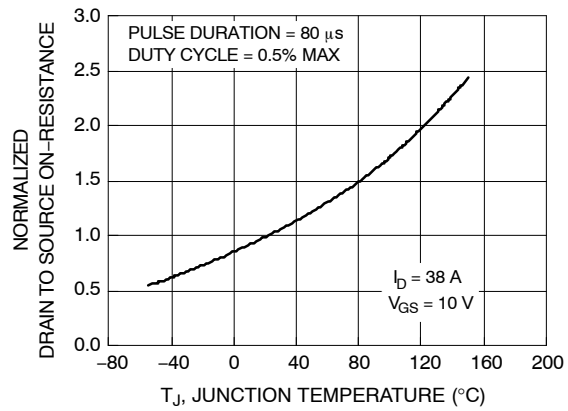
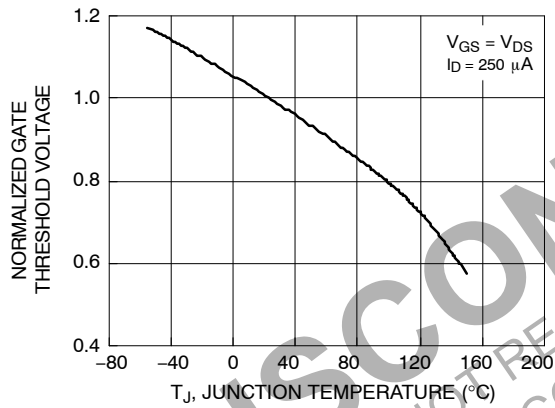
Figure 11.  $R_{DS(on)}$  vs. Gate VoltageFigure 12. Normalized  $R_{DS(on)}$  vs. Junction Temperature

Figure 13. Normalized Gate Threshold Voltage vs. Temperature

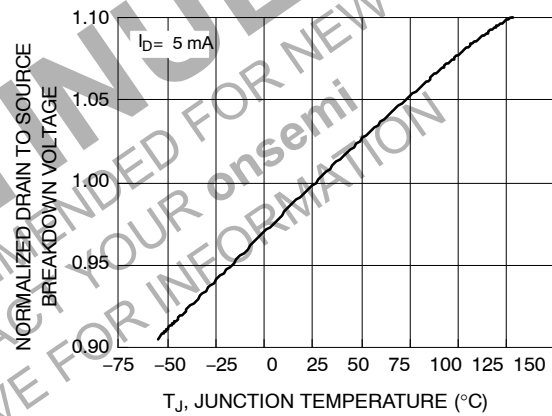


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

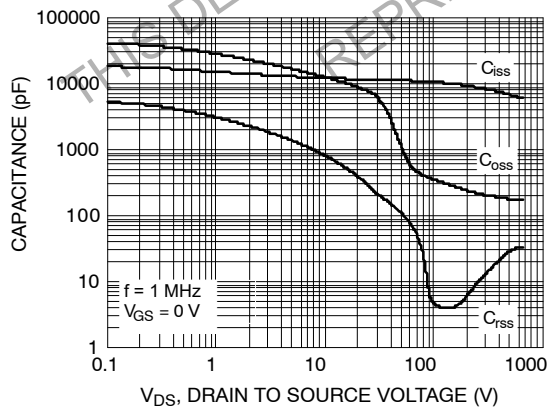


Figure 15. Capacitance vs. Drain to Source Voltage

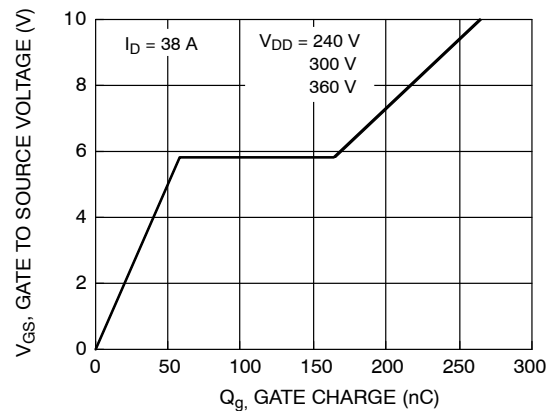


Figure 16. Gate Charge vs. Gate to Source Voltage

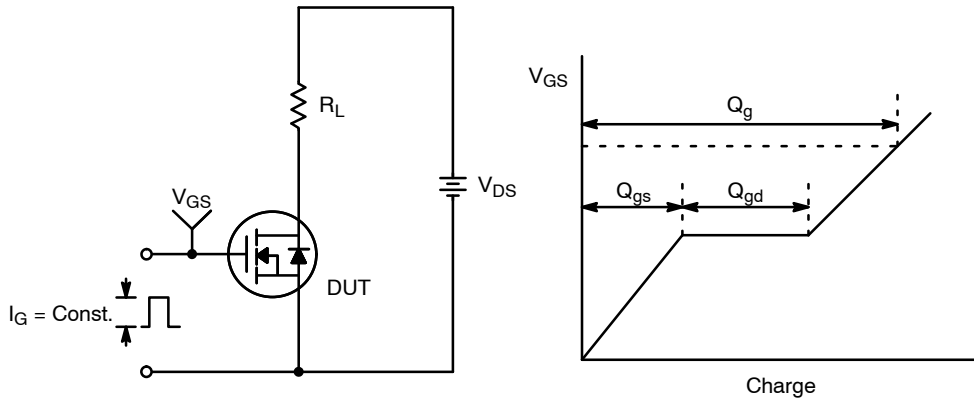


Figure 17. Gate Charge Test Circuit &amp; Waveform

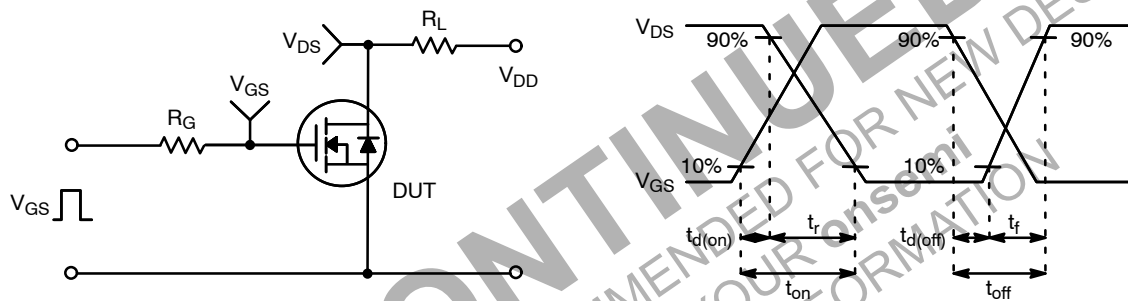


Figure 18. Resistive Switching Test Circuit &amp; Waveforms

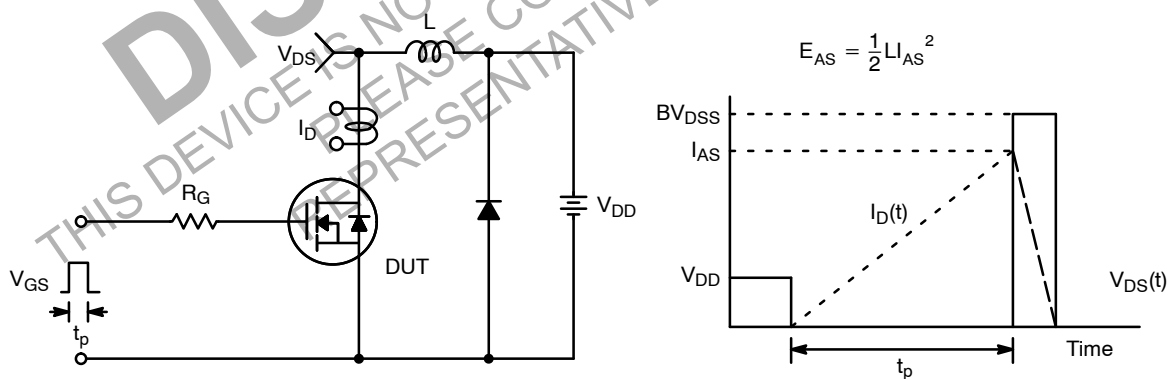


Figure 19. Unclamped Inductive Switching Test Circuit &amp; Waveforms

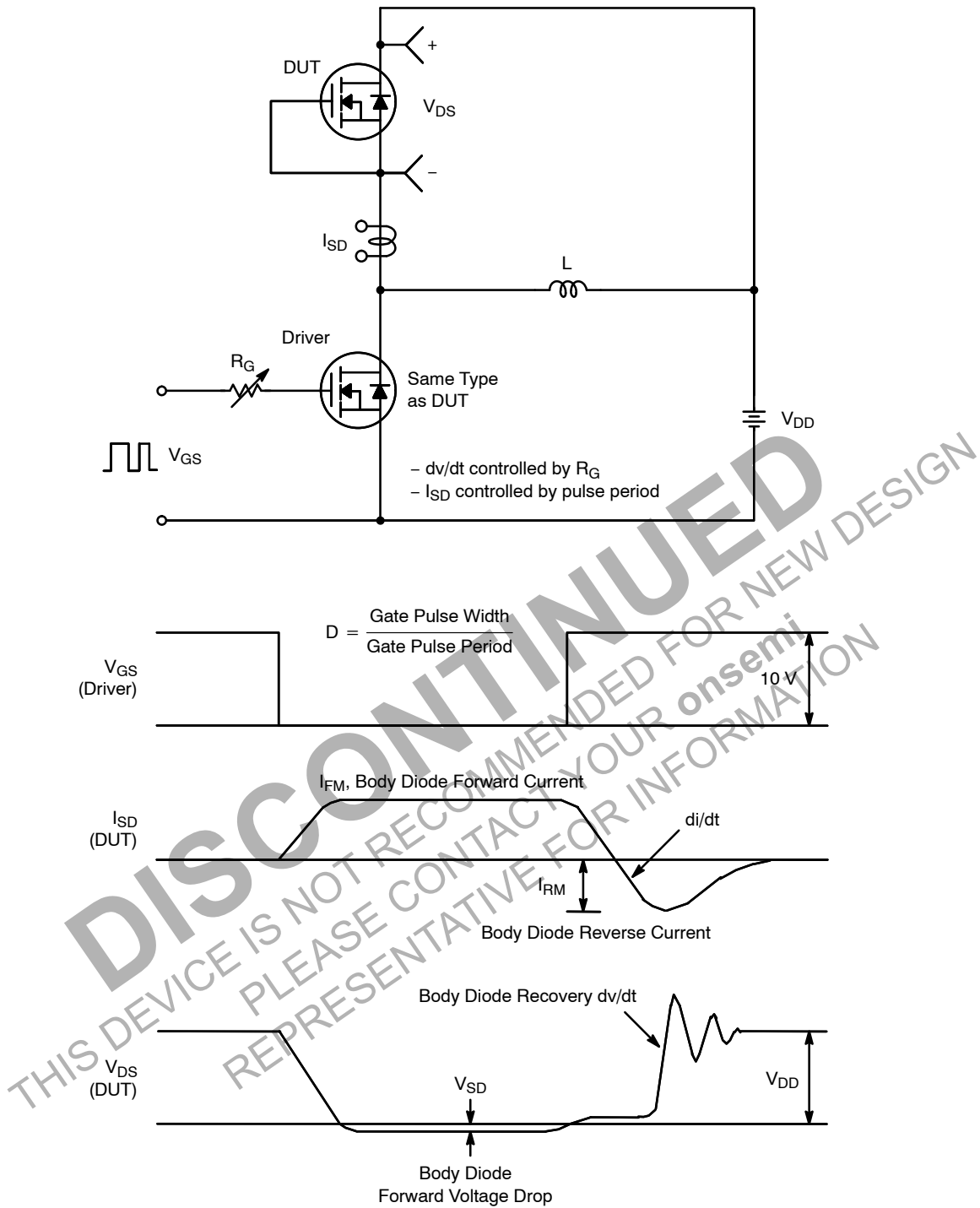


Figure 20. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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**TO-247-3LD SHORT LEAD**  
**CASE 340CK**  
**ISSUE A**

DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.  
B. ALL DIMENSIONS ARE IN MILLIMETERS.  
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.  
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.  
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

**GENERIC**  
**MARKING DIAGRAM\***


XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Assembly Lot Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
ØP1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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